

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/891,325	06/27/2001	Osamu Samuel Nakagawa	10005208-1	3642
75	590 09/27/2005	EXAMINER		
HEWLETT-PACKARD COMPANY			LUU, CHUONG A	
Intellectual Pro	perty Administration			
P.O. Box 272400 Fort Collins, CO 80527-2400			ART UNIT	PAPER NUMBER
			2818	

DATE MAILED: 09/27/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
Office Action Commence	09/891,325	NAKAGAWA, OSAMU SAMUEL			
Office Action Summary	Examiner	Art Unit			
	Chuong A. Luu	2818			
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1: after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period of - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).			
Status					
1)⊠ Responsive to communication(s) filed on Junly	v 18. 2005.				
	<u> </u>				
<u></u>	,—				
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims					
4) ☐ Claim(s) 1-11 is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-11 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	vn from consideration.				
Application Papers					
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomplicant may not request that any objection to the Replacement drawing sheet(s) including the correct	epted or b) objected to by the Eddrawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).			
11) The oath or declaration is objected to by the Ex	animer. Note the attached Office	ACION OF JOHN PTO-152.			
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Application ity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage			
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) Interview Summary Paper No(s)/Mail Da				
Notice of Draitsperson's Patent Drawing Review (PTO-948)	_ ` ` ` `	atent Application (PTO-152)			

Application/Control Number: 09/891,325

Art Unit: 2818

DETAILED ACTION

Response to Arguments

Applicant's arguments with respect to claims 1-11 have been considered but are most in view of the new ground(s) of rejection.

PRIOR ART REJECTIONS

Statutory Basis

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

The Rejections

Claims 1-3, 5 and 7 are rejected under 35 U.S.C. 102(b) as being anticipated by Chung et al. (U.S. 5,757,077).

Chung discloses a semiconductor device with

(1) a first electrode (230) formed during a first deposition of a first metal layer of a multi-level semiconductor device:

a substantially thin dielectric layer (214') configured to be deposited over said first electrode (20);

Application/Control Number: 09/891,325

Art Unit: 2818

a second electrode (218') formed during a second deposition of a second metal layer of said multi-level deposition device, wherein said second electrode (218') is formed over said substantially thin dielectric layer (214'), wherein said on-chip capacitor is formed in a crossover area of said first metal layer (230) and said second metal layer (218') of said multi-level semiconductor device (see Figure 19);

- (2) wherein an angle of intersection between said first metal layer (230) and said second metal layer (218') is between zero and ninety degrees (see Figure 19);
- (3) wherein said first electrode and said second electrode are configured to be substantially parallel (see column 10, lines 56-58);
- (5) wherein said first electrode and said second electrode are configured as a rectangular planar structure (see Figure 19);
- (7) wherein said substantially thin dielectric material comprises a composite of materials (see Figure 19);

Regarding the process limitations recited in claims 1-11 (first and second electrode are formed...), these would not carry patentable weight in this claim drawn to a structure, because distinct structure is not necessarily produced.

Note that a "product by process" claim is directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See also In re Brown, 173 USPQ 685; In re Luck, 177 USPQ 523; In re Fessmann, 180 USPQ 324; In re Avery, 186 USPQ 161; In re Wertheim, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); and In re Marosi et al., 218 USPQ 289; and particularly In re Thorpe, 227 USPQ 964 (Fed. Cir. 1985), all of which make it clear that it is the patentability of

the final product per se which must be determined in a "product by process" claim, and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether claimed in "product by process" claims or not. Note that the applicant has the burden of proof in such cases, as the above case law makes clear. See also MPEP 706.03(e).

PRIOR ART REJECTIONS

Statutory Basis

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

The Rejections

Claims 4, 6 and 10-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chung et al. (U.S. 5,757,077) in view of Johnson (U.S. 6,689,644 B2).

Chung teaches the above outlined features except for different configured shapes of the first and second electrodes such as overlapping; specific material and thickness of the thin dielectric layer. However, Johnson discloses a non-volatile memory device with (4) wherein said first electrode and said second electrode are further configured to be overlapping (see column 18, lines 50-51) (6) wherein said first

electrode and said second electrode are substantially parallel and overlapping; (10) wherein said substantially thin dielectric material layer includes silicon nitride (see column 8, lines 60-61); (11) wherein said thickness of said substantially thin dielectric material layer is between 50 to 100 Å; (8) wherein said material comprises a composite of materials includes PZT and platinum; (9) wherein a dielectric constant of said substantially thin dielectric material layer is substantially high). It would have been obvious to one having ordinary skill in the art at the time the invention was made to combine the teachings of Chung and Johnson to select specific structure configurations as well as material and thickness of the thin dielectric layer for a capacitor structure, since it has been held that the provision of adjustability, where needed, involves only routine skill in the art. In re Stevens, 101 USPQ 284 (CCPA 1954); In re Aller, 105 USPQP 233.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Chuong A. Luu whose telephone number is (571) 272-1902. The examiner can normally be reached on M-F (6:15-2:45).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David C. Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 09/891,325

Art Unit: 2818

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Chuong Anh Luu Patent Examiner September 23, 2005 Page 6